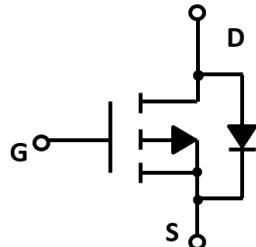

**SOT-23**


### Product Summary

- $V_{DS}$  -30V
- $I_D$  -4.4A
- $R_{DS(ON)}$  (at  $V_{GS}=-10V$ ) <55 mohm
- $R_{DS(ON)}$  (at  $V_{GS}=-4.5V$ ) <68 mohm
- $R_{DS(ON)}$  (at  $V_{GS}=-2.5V$ ) <96 mohm

### General Description

- Trench Power LV MOSFET technology
- High density cell design for Low  $R_{DS(ON)}$
- High Speed switching

### Applications

- Battery protection
- Load switch
- Power management

### ■ Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Maximum	Unit
Drain-source Voltage		$V_{DS}$	-30	V
Gate-source Voltage		$V_{GS}$	$\pm 12$	V
Drain Current	$T_A=25^\circ\text{C}$ @ Steady State	$I_D$	-4.4	A
	$T_A=70^\circ\text{C}$ @ Steady State		-3.5	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	-27	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$		$P_D$	1.2	W
Thermal Resistance Junction-to-Ambient @ Steady State <sup>B</sup>		$R_{\theta JA}$	105	$^\circ\text{C} / \text{W}$
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 ~ +150	$^\circ\text{C}$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
SE3401	F2	3401.	3000	30000	120000	7" reel



Leiditech

SE3401

■ Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30			V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}, T_c=25^\circ\text{C}$			-1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}= \pm 12\text{V}, V_{\text{DS}}=0\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}= V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.6	-0.9	-1.4	V
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}= -10\text{V}, I_{\text{D}}=-4.4\text{A}$		45.5	55	mΩ
		$V_{\text{GS}}= -4.5\text{V}, I_{\text{D}}=-4\text{A}$		52	68	
		$V_{\text{GS}}= -2.5\text{V}, I_{\text{D}}=-2\text{A}$		64	96	
Diode Forward Voltage	$V_{\text{SD}}$	$I_{\text{S}}=-4.4\text{A}, V_{\text{GS}}=0\text{V}$		-0.8	-1.2	V
Maximum Body-Diode Continuous Current	$I_{\text{S}}$				-4.4	A
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		680		pF
Output Capacitance	$C_{\text{oss}}$			105		
Reverse Transfer Capacitance	$C_{\text{rss}}$			68		
<b>Switching Parameters</b>						
Total Gate Charge	$Q_{\text{g}}$	$V_{\text{GS}}=-10\text{V}, V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-4.4\text{A}$		7.2		nC
Gate Source Charge	$Q_{\text{gs}}$			1.2		
Gate Drain Charge	$Q_{\text{gd}}$			1.6		
Turn-on Delay Time	$t_{\text{D(on)}}$	$V_{\text{GS}}=-10\text{V}, V_{\text{DD}}=-15\text{V}, R_L=15\Omega, I_{\text{D}}=-1\text{A}, R_{\text{GEN}}=2.5\Omega$		15		ns
Turn-on Rise Time	$t_r$			63		
Turn-off Delay Time	$t_{\text{D(off)}}$			21		
Turn-off Fall Time	$t_f$			12		

A. Pulse Test: Pulse Width  $\leq 300\text{us}$ , Duty cycle  $\leq 2\%$ .

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

## ■ Typical Performance Characteristics

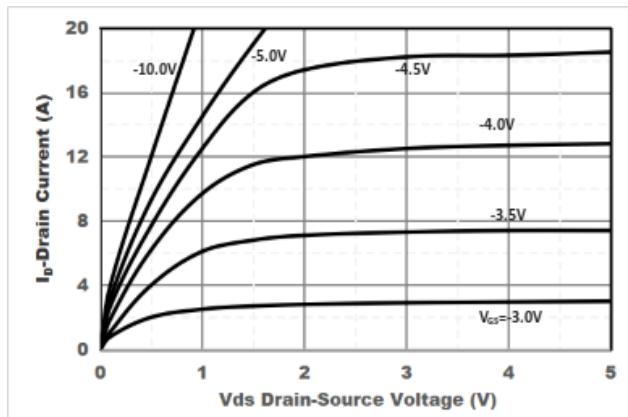


Figure1. Output Characteristics

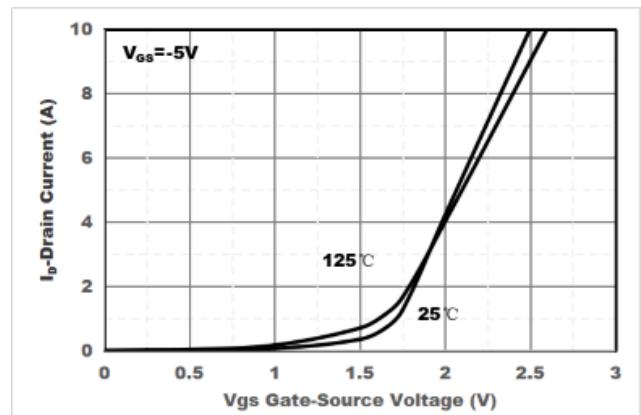


Figure2. Transfer Characteristics

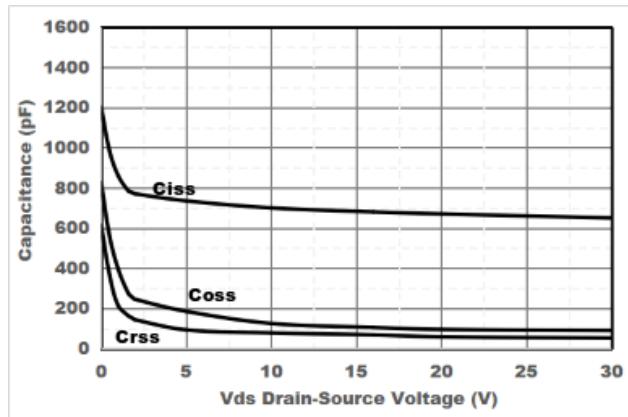


Figure3. Capacitance Characteristics

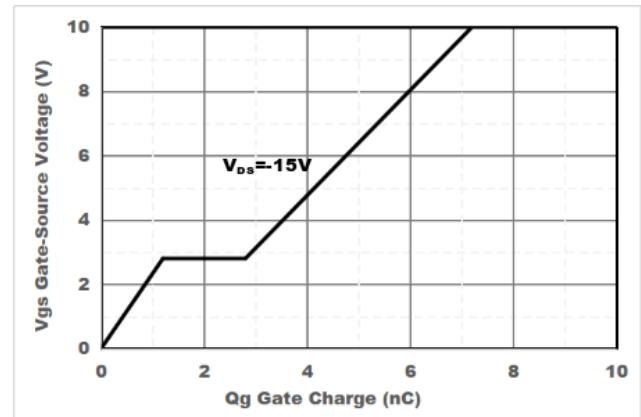


Figure4. Gate Charge

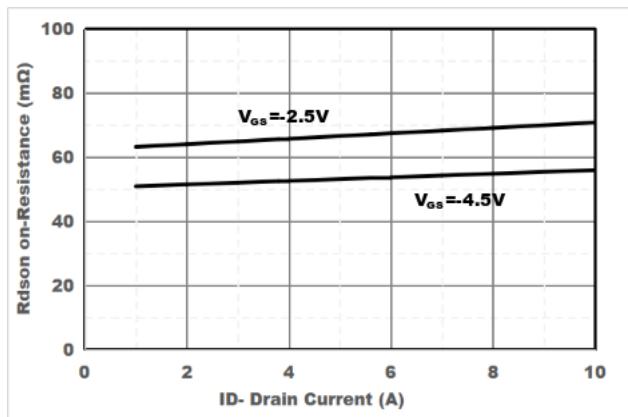


Figure5. Drain-Source on Resistance

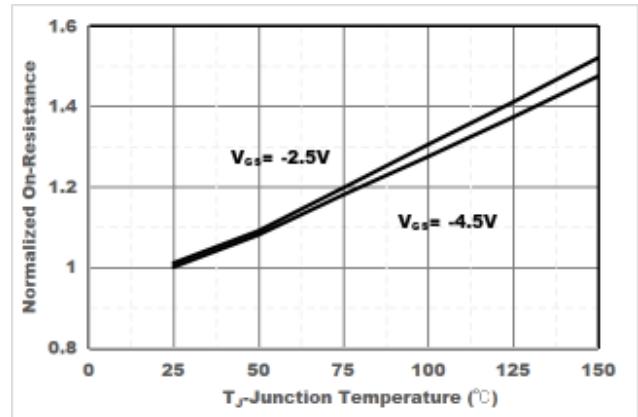


Figure6. Drain-Source on Resistance

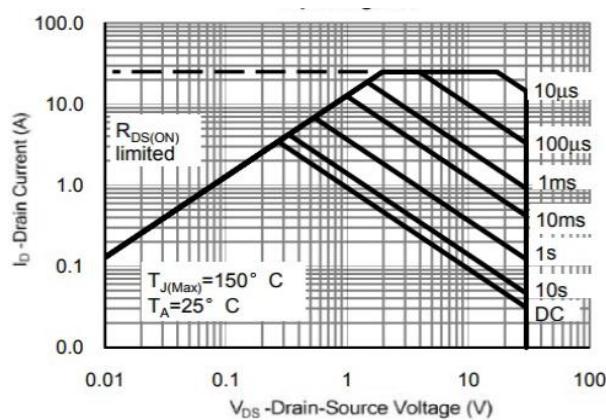


Figure7. Safe Operation Area

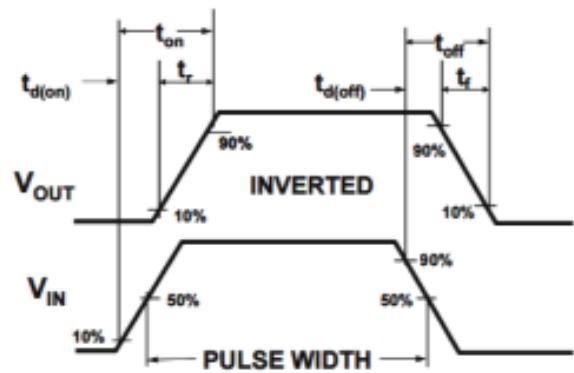
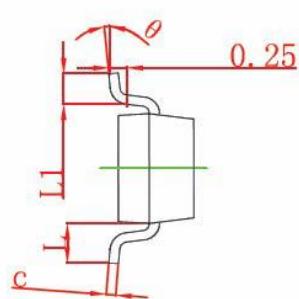
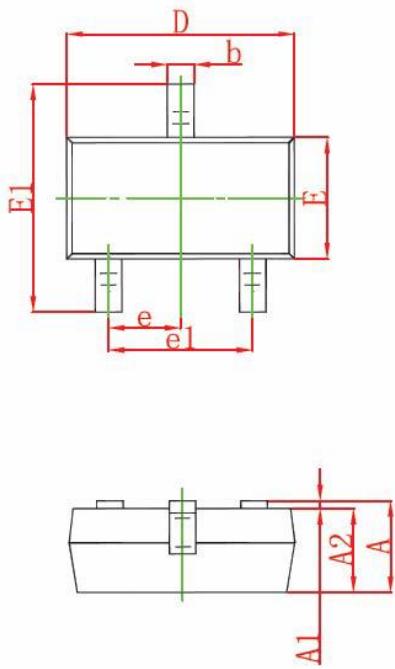


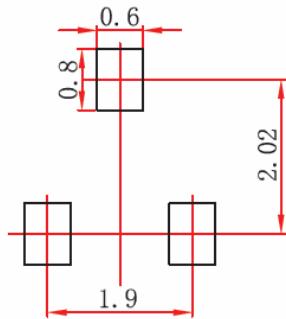
Figure8. Switching wave

## ■ SOT-23 Package information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

## ■ SOT-23 Suggested Pad Layout



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance:  $\pm 0.05\text{mm}$ .  
 3. The pad layout is for reference purposes only.

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